

ABSTRACT

A method for removing a polysilicon layer from a non-silicon layer comprising the following steps. A structure having a non-silicon layer formed thereover is provided. A first polysilicon layer is formed upon the non-silicon layer. The first polysilicon layer is removed from over the non-silicon layer to expose the non-silicon layer using a NH_4OH :DIW dip solution process having a NH_4OH :DIW ratio of from about 1:2 to 1:8. Whereby the non-silicon layer is substantially unaffected by the NH_4OH :DIW dip solution process.

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